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Sanken SANKEN ELECTRIC MLD685D

Feb. 2011

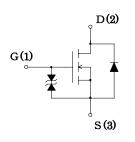
Features Package • Low on-state resistance MT100 (TO3P) • Built-in gate protection diode Image: Comparison of the state o

• High current switching

Key Specifications

- V(BR)DSS=60V (ID=100µA)
- RDS(ON)=4.7m Ω Max. (VGS=10V,ID=42A)

Internal Equivalent Circuit



Absolute maximum ratings

Characteristic	Symbol	Rating	Unit
Drain to Source Voltage	$V_{\rm DSS}$	60	V
Gate to Source Voltage	$\mathbf{V}_{\mathrm{GSS}}$	±20	V
Continuous Drain Current	ID	± 85	А
Pulsed Drain Current	${ m I}_{ m D(pulse)}$ $^{st 1}$	± 280	А
Maximum Power Dissipation	PD	150 (Tc=25°C)	W
Single Pulse Avalanche Energy	${ m E_{AS}}^{st_2}$	280	mJ
Channel Temperature	Tch	-55~150	°C
Storage Temperature	Tstg	-55~150	°C

 $\%1~\mathrm{PW}\!\leq\!100\,\mu$ sec. duty cycle $\leq\!1\%$

*2 VDD=20V, L=1mH, IL=20A, unclamped, See Fig.1

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Electrical characteristics

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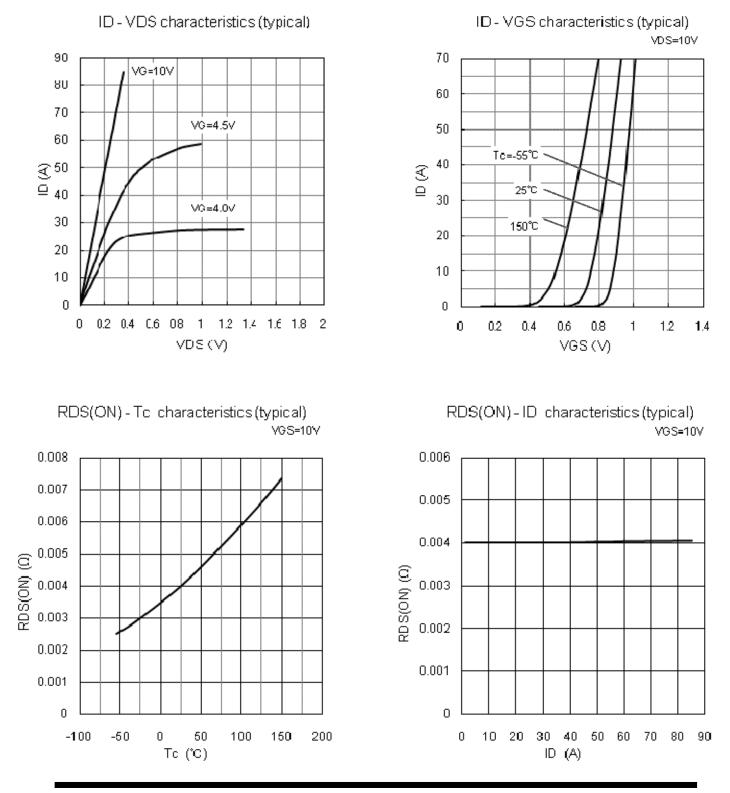
					(Ta	a=25°C)
Characteristic	Symbol	Test Conditions	Limits			Unit
			MIN	TYP	MAX	Unit
Drain to Source breakdown Voltage	V _{(BR)DSS}	I _D =100µA,V _{GS} =0V	60			V
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±20V			±10	μA
Drain to Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			100	μA
Gate Threshold Voltage	V _{TH}	V _{DS} =10V, I _D =1mA	2.0	2.5	3.0	V
Forward Transconductance	Re(yfs)	V _{DS} =10V, I _D =42A	30			S
Static Drain to Source On-Resistance	R _{DS(ON)}	I _D =42A, V _{GS} =10V		4.0	4.7	mΩ
Input Capacitance	Ciss	V _{DS} =10V V _{GS} =0V f=1MHz		11500		pF
Output Capacitance	Coss			1500		
Reverse Transfer Capacitance	Crss			1100		
Turn-On Delay Time	td(on)	I _D =42A, V _{DD} 16V - R _G =22Ω, V _{GS} =10V See Fig.2		60		- ns
Rise Time	tr			25		
Turn-Off Delay Time	td(off)			370		
Fall Time	tr			65		
Source-Drain Diode Forward Voltage	V _{SD}	I _{SD} =50A,V _{GS} =0V		0.87	1.5	V
Source-Drain Diode Reverse Recovery Time	trr	I _{SD} =50A di/dt=100A/us		70		ns

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Characteristic Curves (Tc=25°C)

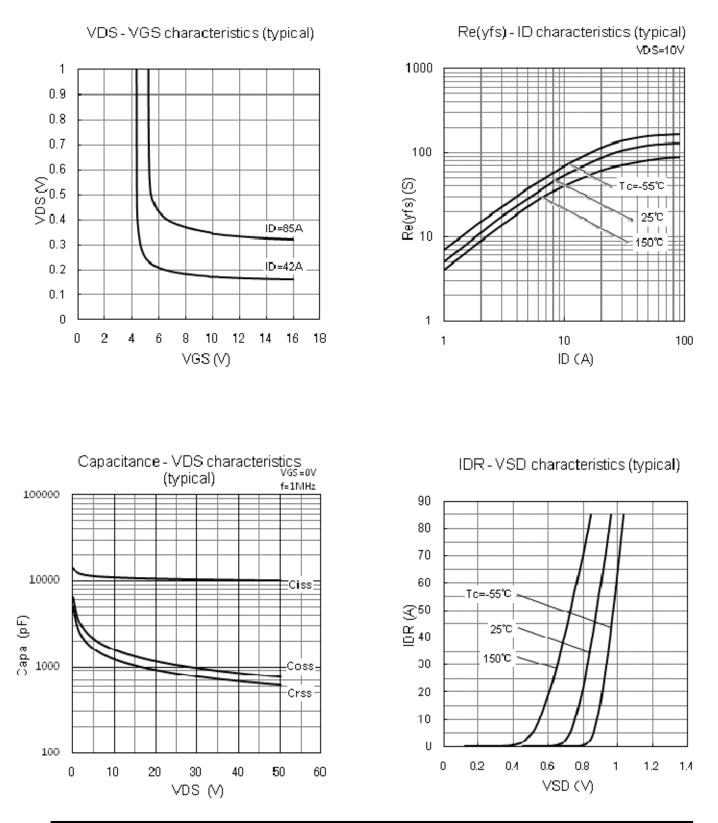


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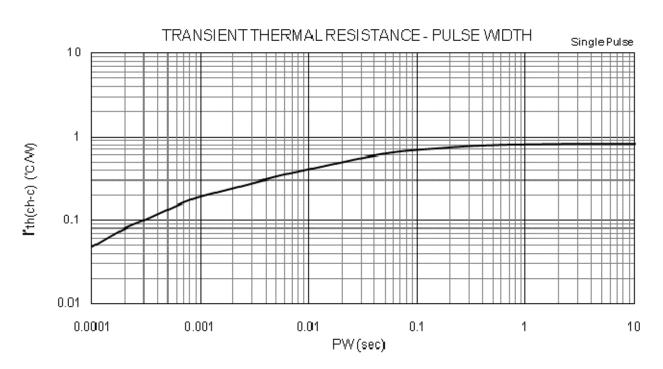


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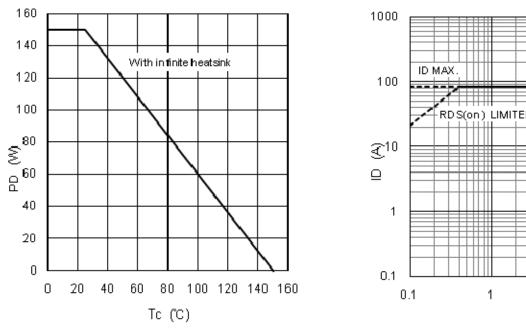
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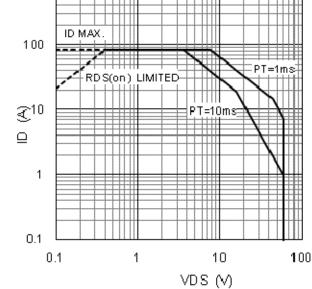
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Characteristic Curves (Tc=25°C)



PD-Tc characteristics



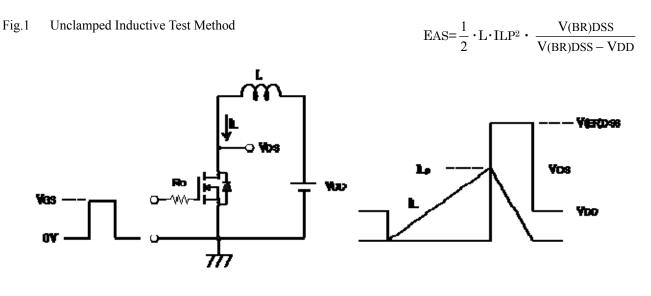


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Tc=25℃ Single Pulse

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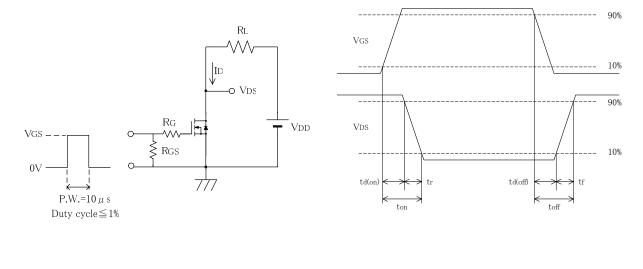
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(a) Test Circuit

(b) Waveforms

Fig.2 Switching Time Test Method



(a) Test Circuit

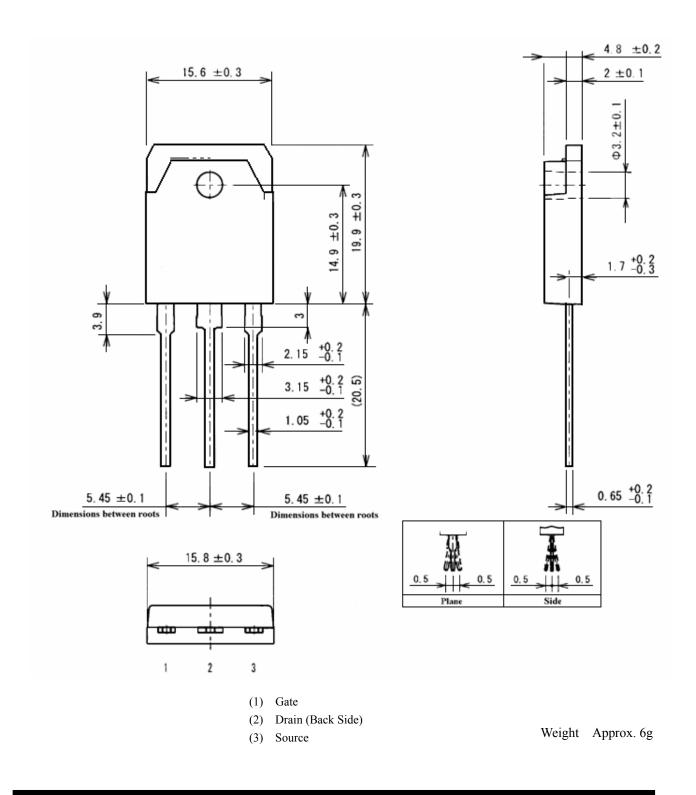
(b) Waveforms

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<u>Outline</u>

MT100 (TO3P)



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